

## VS-2EQH01HM3, VS-2EQH02HM3

Vishay Semiconductors

AUTOMOTIVE

COMPLIANT HALOGEN

FREE

# **Ultrafast Rectifier, 2 A FRED Pt®**

# eSMP® Series





Top View Bottom View

#### MicroSMP (DO-219AD)

Anode O Cathode

### **LINKS TO ADDITIONAL RESOURCES**



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	2 A			
$V_{R}$	100 V, 200 V			
V <sub>F</sub> at I <sub>F</sub>	0.82 V			
t <sub>rr</sub> (typ.)	33 ns			
I <sub>FSM</sub>	30 A			
T <sub>J</sub> max.	175 °C			
Package	MicroSMP (DO-219AD)			
Circuit configuration	Single			

#### **FEATURES**

- Very low profile typical height of 0.65 mm
- · Ideal for automated placement
- · Low forward voltage drop, low power losses
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- For PFC, CRM snubber operation
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### TYPICAL APPLICATIONS

For use in high frequency, freewheeling, DC/DC converters, PFC, and in snubber industrial and automotive applications.

#### **MECHANICAL DATA**

Case: MicroSMP (DO-219AD)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per

J-STD-002, meets JESD 201 class 2 whisker test

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage VS-2EQH01HM3	V <sub>RRM</sub>		100	V		
VS-2EQH02HM3			200			
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>M</sub> = 137 °C	2	۸		
Non-repetitive peak surge current	I <sub>FSM</sub>	$T_J = 25$ °C, 10 ms sine pulse	30	A		
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C		

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage,	VS-2EQH01HM3	$V_{BR}$ ,	Ι <sub>R</sub> = 100 μΑ	100	-	-	
blocking voltage VS-2E	VS-2EQH02HM3	$V_R$		200			V
Forward voltage		V <sub>F</sub>	I <sub>F</sub> = 2 A	-	0.96	1.05	
	v <sub>F</sub>	I <sub>F</sub> = 2 A, T <sub>J</sub> = 150 °C	-	0.82	0.84		
Reverse leakage current		,	$V_R = V_R$ rated	1			
		IR	$T_J = 150 ^{\circ}\text{C},  V_R = V_R  \text{rated}$	-	-	25	μΑ
Junction capacitance		C <sub>T</sub>	V <sub>R</sub> = 200 V	-	6	-	pF

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	33	-	
Reverse recovery time t <sub>rr</sub>		$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	-	23	
	ιm	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 2 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 100 V	-	19	-	ns A nC
		T <sub>J</sub> = 125 °C		-	33	-	
Peak recovery current I <sub>RRM</sub>	ı	T <sub>J</sub> = 25 °C		-	1.7	-	
	IRRM	T <sub>J</sub> = 125 °C		-	2.5	-	
Reverse recovery charge Q <sub>rr</sub>	0	$T_J = 25  ^{\circ}C$		-	15	-	
	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	34	-	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and s	storage temperature	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C
Thermal resistance, junction to mount		R <sub>thJM</sub> <sup>(1)</sup>		-	16	20	
Thermal resistance, junction to ambient		R <sub>thJA</sub>	Device mounted on FR4 PCB, 2 oz. standard footprint	-	160	-	°C/W
Approximate weight					0.006		g
Marking device VS-2EQH01HM3 VS-2EQH02HM3		Case style MicroSMP (DO-219AD)		2H1			
				2H2			

#### Note

<sup>(1)</sup> Thermal resistance junction to mount follows JEDEC® 51-14 transient dual interface test method (TDIM)

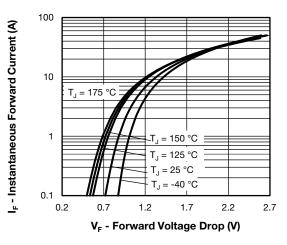


Fig. 1 - Typical Forward Voltage Drop Characteristics

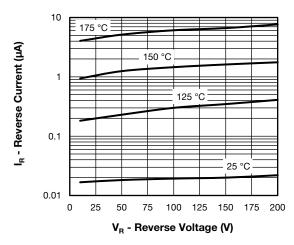


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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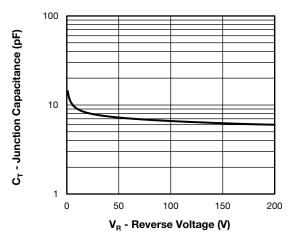


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

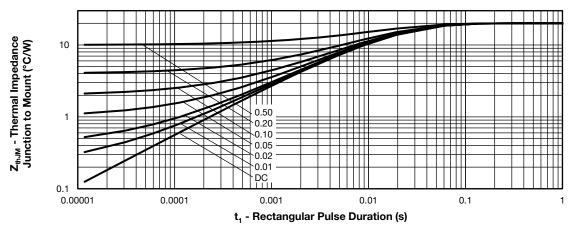


Fig. 4 - Maximum Transient Thermal Impedance, Junction to Mount

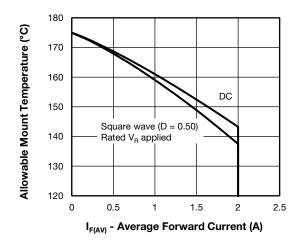


Fig. 5 - Maximum Allowable Mount Temperature vs. Average Forward Current

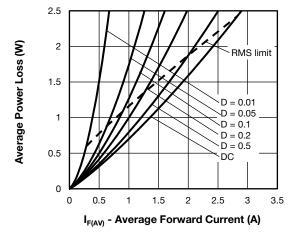
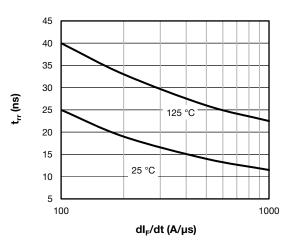


Fig. 6 - Forward Power Loss Characteristics

#### Note

Formula used:  $T_M = T_J - (Pd + Pd_{REV}) \times R_{thJM}$ ;  $Pd = forward power loss = I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig. 5);  $Pd_{REV} = inverse power loss = V_{R1} \times I_R$  (1 - D);  $I_R$  at  $V_{R1} = rated V_R$ 

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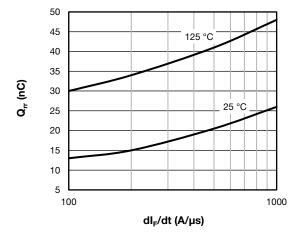
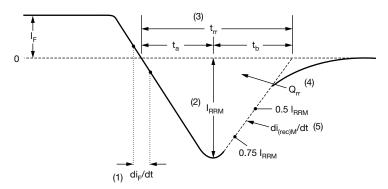


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

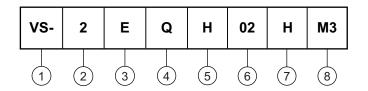
Fig. 9 - Reverse Recovery Waveform and Definitions

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#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - Current rating (2 = 2 A)

Circuit configuration:

E = single diode

Q = MicroSMP package

5 - Process type,

H = ultrafast recovery

Voltage code (02 = 200 V)

7 - H = AEC-Q101 qualified

8 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N PREFERRED PACKAGE CODE MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-2EQH01HM3/H	Н	4500	7" diameter plastic tape and reel			
VS-2EQH02HM3/H	Н	4500	7" diameter plastic tape and reel			

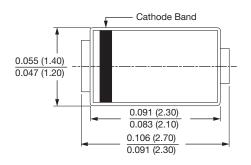
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?96591</u>					
Part marking information	www.vishay.com/doc?96590				
Packaging information	www.vishay.com/doc?88869				
SPICE model	www.vishay.com/doc?96595				

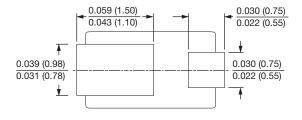


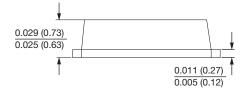
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# MicroSMP (DO-219AD), FRED Pt®

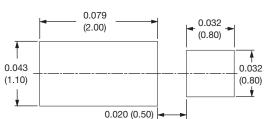
#### **DIMENSIONS** in inches (millimeters)







### Mounting Pad Layout





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